

COMPLEMENTARY NPN / PNP SMALL SIGNAL TRANSISTOR IN SOT363

Features & Benefits

- Complementary Pairs:
 - One 2222A Type (NPN)
 - One 2907A Type (PNP)
- Ideal for Low-Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMDT2227Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

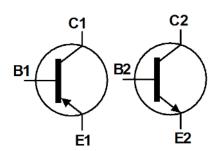
https://www.diodes.com/quality/product-definitions/

Mechanical Data

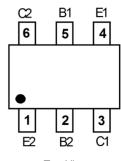
- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (approximate)







Device Symbol



Top View Pin-Out

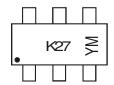
Ordering Information (Note 4)

Orderable Part Number	Marking	Reel size (inches)	Tape width (mm)	Pack	ing
Orderable Part Number	Warking	neer size (inches)	rape width (min)	Quantity	Carrier
MMDT2227Q-7-F	K27	7	8	3,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \text{K27} = \text{Product Type Marking Code} \\ \text{YM} = \text{Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: K} = 2023) \\ \text{M or } \overline{\text{M}} = \text{Month (ex: 2} = \text{February)} \end{array}$

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	T	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings, 2222A Type (NPN) (@ T_{amb} = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	600	mA

Maximum Ratings, 2907A Type (PNP) (@ T_{amb} = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	Ic	-600	mA

Thermal Characteristics (@ T_{amb} = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ hetaJA}$	625	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	150	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For the device mounted on minimum recommended pad layout FR-4, device is measured under still air conditions whilst operating in a steady-state.

6. Thermal resistance from junction to the top of package.

7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristic and Derating Information

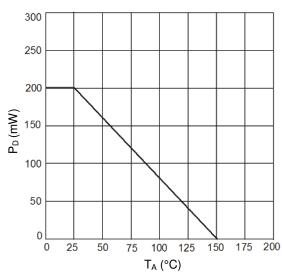


Figure 1. P_D v T_A

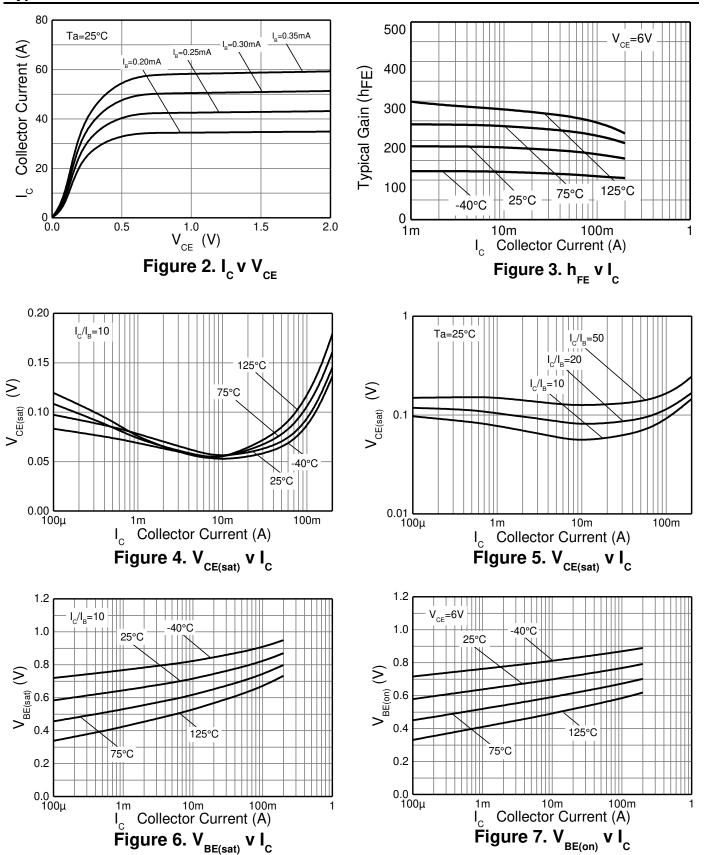


Electrical Characteristics, 2222A Type (NPN) (@ T_{amb} = +25°C, unless otherwise specified.)

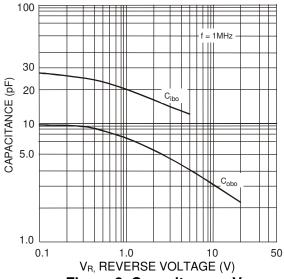
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV _{CBO}	75		V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_	V	$I_E = 100\mu A$
Collector Cutoff Current	I _{CBO}		10	nA μA	$V_{CB} = 60V$ $V_{CB} = 60V$, $T_{amb} = +150$ °C
Collector Cutoff Current	I _{CEX}	_	10	nA	V _{CE} = 60V, V _{EB(off)} = 3.0V
Emitter Cutoff Current	I _{EBO}	_	10	nA	V _{EB} = 5.0V
Base Cutoff Current	I _{BL}	_	20	nA	$V_{CE} = 60V, V_{EB(off)} = 3.0V$
ON CHARACTERISTICS (Note 8)				l	. ==(=::)
DC Current Gain	h _{FE}	35 50 75 100 40 50 35	 300 		$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 10V \\ I_C &= 1mA, \ V_{CE} = 10V \\ I_C &= 10mA, \ V_{CE} = 10V \\ I_C &= 150mA, \ V_{CE} = 10V \\ I_C &= 500mA, \ V_{CE} = 10V \\ I_C &= 10mA, \ V_{CE} = 10V, \ T_{amb} = -55^{\circ}C \\ I_C &= 150mA, \ V_{CE} = 1V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.3 1.0	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.6	1.2 2.0	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}		8	pF	$V_{CB} = 10V$, $f = 1MHz$
Input Capacitance	C _{ibo}		25	pF	$V_{EB} = 0.5V$, $f = 1MHz$
Current Gain-Bandwidth Product	f⊤	300		MHz	$V_{CE} = 20V$, $I_C = 20mA$, $f = 100MHz$
Noise Figure	NF		4.0	dB	$V_{CE} = 10V, I_{C} = 100\mu A,$ $R_{S} = 1k\Omega, f = 1kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	10	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	t _r		25	ns	$V_{BE(off)} = -0.5V, I_{B1} = 15mA$
Storage Time	ts		225	ns	$V_{CC} = 30V, I_C = 150mA,$
Fall Time	t _f		60	ns	$I_{B1} = -I_{B2} = 15mA$

Note: 8. Pulse test: Pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.











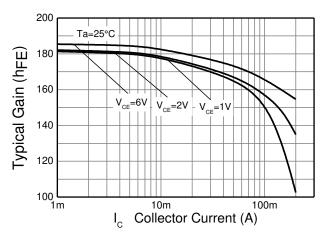


Figure 10. $h_{FE} v l_{C}$

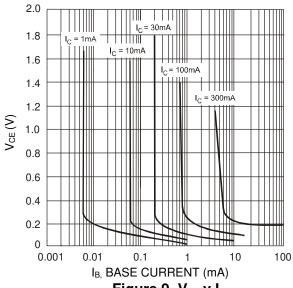


Figure 9. V_{CE} v I_B



Electrical Characteristics, 2907A Type (PNP) (@T_{amb} = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)					
Collector-Base Breakdown Voltage	BV _{CBO}	-60	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	-60	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	_	-10	nA μA	$V_{CB} = -50V$ $V_{CB} = -50V$, $T_{amb} = +125^{\circ}C$
Collector Cutoff Current	I _{CEX}	_	-50	nΑ	$V_{CE} = -30V$, $V_{EB(off)} = -0.5V$
Base Cutoff Current	I _{BL}	_	-50	nA	$V_{CE} = -30V, V_{EB(off)} = -0.5V$
ON CHARACTERISTICS (Note 9)				l	, ==,(=:,)
DC Current Gain	h _{FE}	75 100 100 100 50	 300 	_	$\begin{split} & I_{C} = -100 \mu A, \ V_{CE} = -10V \\ & I_{C} = -1.0 m A, \ V_{CE} = -10V \\ & I_{C} = -10 m A, \ V_{CE} = -10V \\ & I_{C} = -150 m A, \ V_{CE} = -10V \\ & I_{C} = -500 m A, \ V_{CE} = -10V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-0.4 -1.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-1.3 -2.6	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_obo	_	8.0	pF	V _{CB} = -10V, f = 1MHz
Input Capacitance	C _{ibo}		30	pF	$V_{EB} = -2V$, $f = 1MHz$
Current Gain-Bandwidth Product	f _T	200	_	MHz	$V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}		45	ns	_
Delay Time	t _d		10	ns	$V_{CC} = -30V, I_{C} = -150mA,$
Rise Time	t _r		40	ns	$I_{B1} = -15mA$
Turn-Off Time	t _{off}	_	100	ns	
Storage Time	ts		80	ns	$V_{CC} = -6V, I_{C} = -150mA,$
Fall Time	t _f	_	30	ns	$I_{B1} = I_{B2} = -15mA$

Note: 9. Short duration pulse test used to minimize self-heating effect.



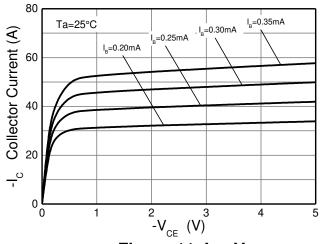
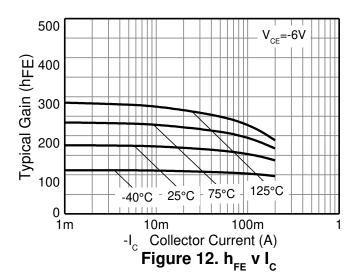


Figure 11. I_c v V_{CE}



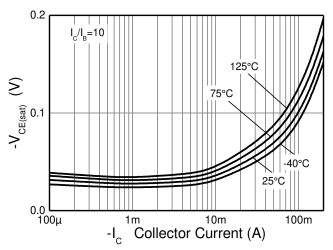


Figure 13. $V_{CE(sat)} V I_{C}$

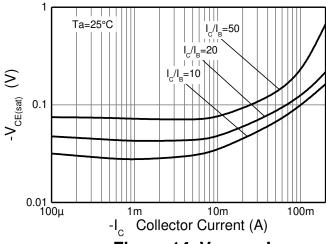


Figure 14. V_{CE(sat)} v I_C

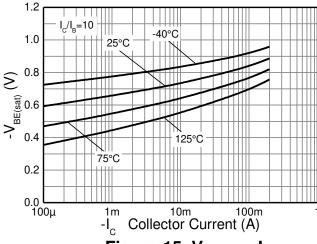


Figure 15. $V_{\rm BE(sat)} v I_{\rm C}$

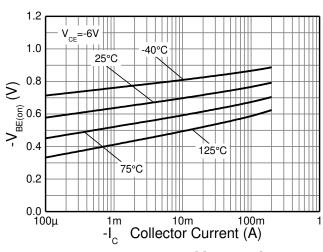


Figure 16. $V_{\rm BE(on)} V I_{\rm C}$



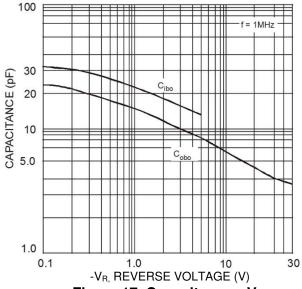
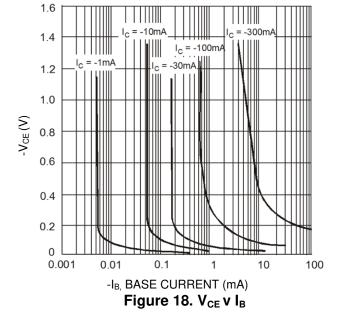
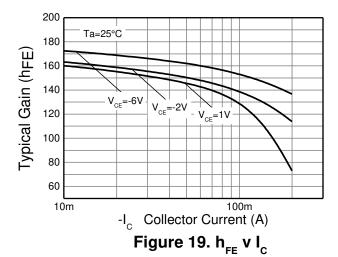


Figure 17. Capacitance v V_R





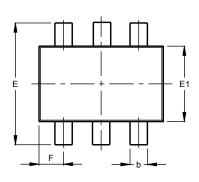
MMDT2227Q Document number: DS40088 Rev. 2 - 2

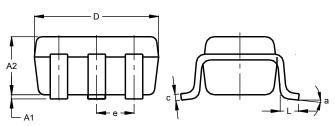


Package Outline Dimensions

Please see https://www.diodes.com/design/support/packaging/diodes-packaging/ for the latest version.

SOT363



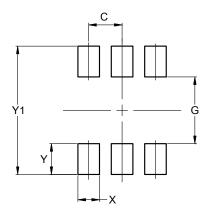


SOT363						
Dim	Min	Max	Тур			
A 1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
C	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All I	All Dimensions in mm					

Suggested Pad Layout

Please see https://www.diodes.com/design/support/packaging/diodes-packaging/ for the latest version.

SOT363



Dimensions	Value
Dillielisiolis	(in mm)
С	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500



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